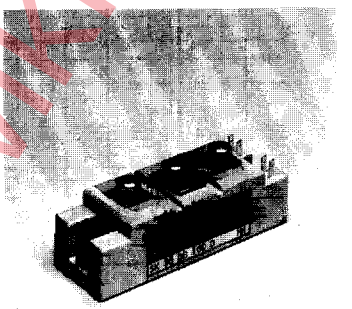
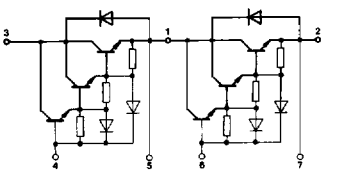
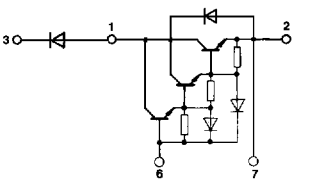
SEMITRANS® 2 NPN
Power Darlington Modules
30 A, 1000 V

SK 30 DB 100 D
SK 30 DAL 100 D





DB



DAL

Maximum Ratings

Symbol	Conditions	Values	Units
V_{CEVsus}	I_C = 1 A, V_{BE} = – 2 V	1000	V
V_{CEV}	V_{BE} = – 2 V	1000	V
V_{CBO}	I_E = 0	1000	V
V_{EBO}	I_C = 0	7	V
I_C	D. C.	30	A
I_{CM}	t_p = 1 ms	60	A
I_F = –I_C	D. C.	30	A
I_B		2	A
P_{TOT}	T_{case} = 25 °C, per darlington	310	W
T_{vj}		– 40 . . . + 150	°C
T_{stg}		– 40 . . . + 125	°C
V_{isol}	a. c. 50 Hz, r.m.s.	2500~	V

Thermal Characteristics

R_{thjc}	per darlington/per module	0,4/0,2	°C/W
R_{thjc}	per diode/per module	1,5/0,75	°C/W
R_{thch}	per ½ module/per module	0,15/0,075	°C/W

Electrical Characteristics[1)]

			min.	typ.	max.	
I_{CEV}	V_{CE} = V_{CEV}, V_{BE} = – 2 V				1	mA
I_{EBO}	I_C = 0, V_{BE} = – 7 V				200	mA
V_{CEsat}[2)]	I_C = 30 A, I_B = 0,6 A				2,5	V
V_{BEsat}[2)]	I_C = 30 A, I_B = 0,6 A				3,5	V
h_{21E}[2)]	I_C = 30 A	V_{CE} = 2,8 V	75			
		V_{CE} = 5 V	100			

Switching Characteristics for Resistive Load[1)]

t_{on}	I_C = 30 A		0,7	2,5	µs
t_s	I_{B1} = – I_{B2} = 0,6 A		11	15	µs
t_f	V_{CC} = 600 V		1,2	3,0	µs

Inverse Diode Characteristics[1)]

V_F = –V_{CE}	I_F = – I_C = 30 A				1,8	V
I_{FSM} = – I_{Cp}	sin 180°, 10 ms	300				A
I_{RM}	I_F = – I_C = 30 A, – di_F/dt = 100 A/µs V_{BE} = – 3 V, V_R = V_{CE} = 400 V, T_{vj} = 125 °C			30		A
Q_{rr}				15		µC

Mechanical Data

M_1	Case to heatsink	SI units	3		6	Nm
		US units	27		53	lb. in.
M_2	Busbars to terminals	SI units	2,5		5	Nm
		US units	22		44	lb. in.
w				250		g
Case		DB		D 11		
		DAL		D 21		

Features

- Isolated baseplate (ease of mounting of one or several modules on one heatsink)
- All electrical connections on top (ease of interconnecting of modules with busbars/PCB)
- Large clearances and creepage distances
- Parallel connected fast recovery inverse diode
- UL recognized, file no. 63 532

Typical Applications

- Switched mode power supplies
- DC servo and robot drives
- AC motor controls
- Brake choppers (DAL)

1) T_{case} = 25 °C unless otherwise stated
2) $t_p \leq 300$ µs, D ≤ 1,5 %

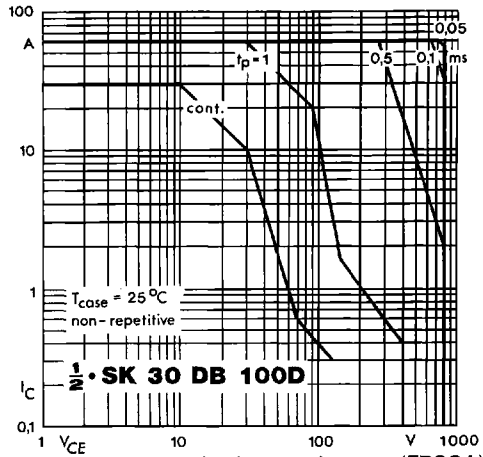


Fig. 1 Forward biased safe operating area (FBSOA)

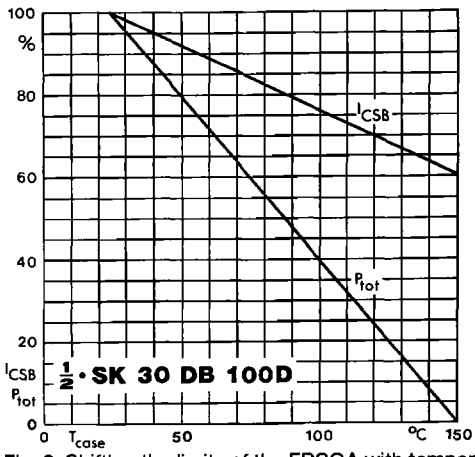


Fig. 2 Shifting the limits of the FBSOA with temperature

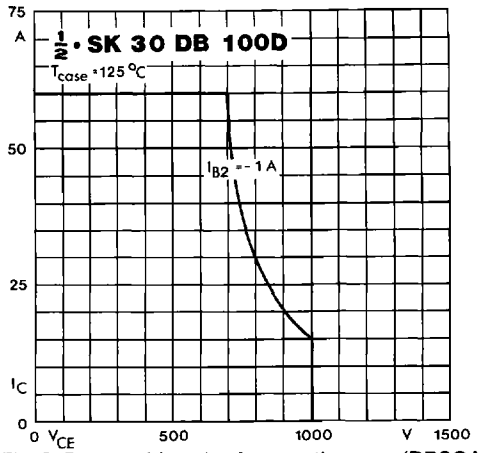


Fig. 3 Reverse biased safe operating area (RBSOA)

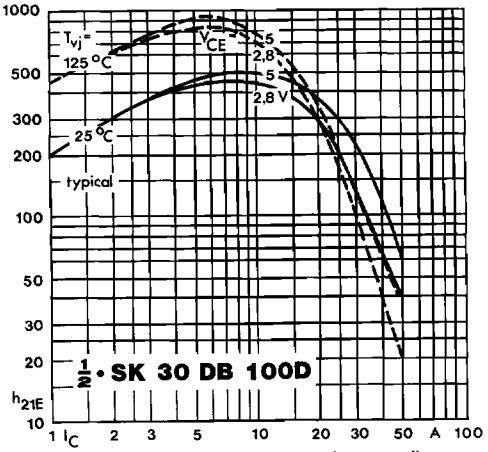


Fig. 4 Forward current transfer ratio vs. coll. current

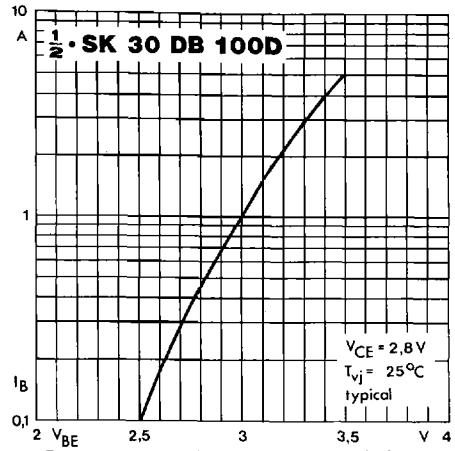


Fig. 5 Base current/voltage characteristic

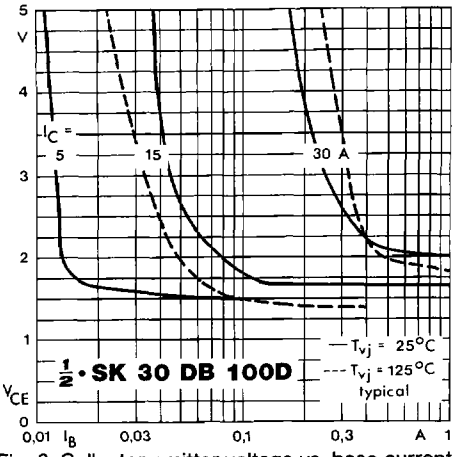


Fig. 6 Collector-emitter voltage vs. base current

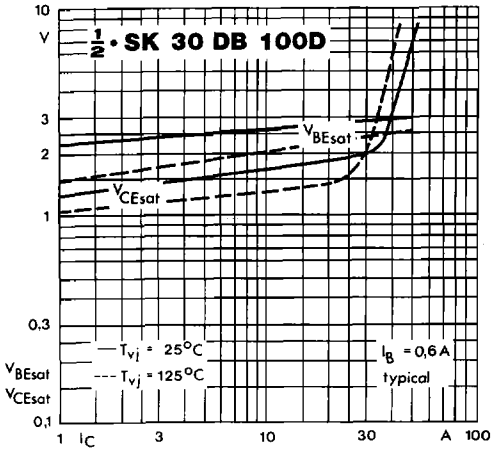


Fig. 7 Saturation voltages vs. collector current

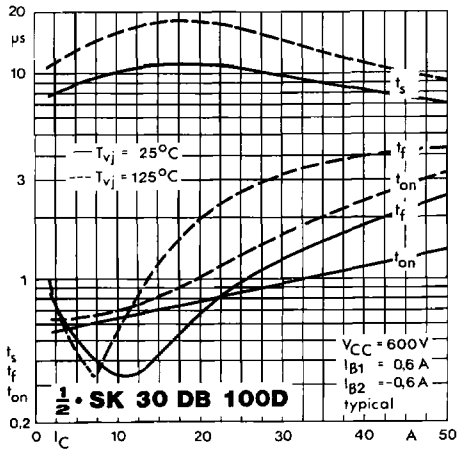


Fig. 8 Switching times vs. collector current

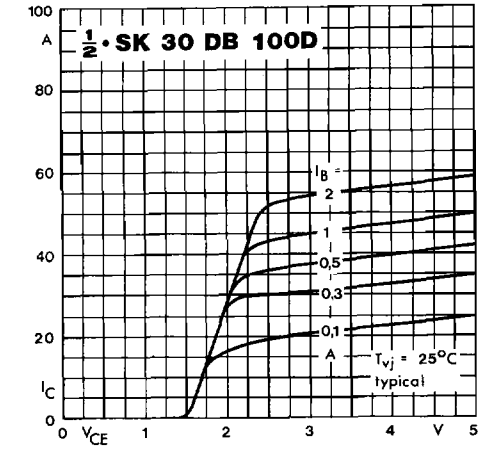


Fig. 9 Collector current/voltage characteristics

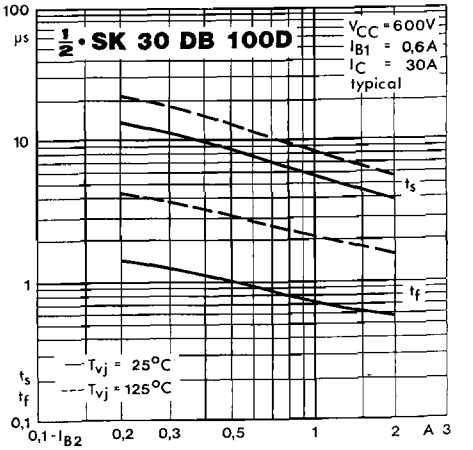


Fig. 10 Turn-off times vs. negative base current

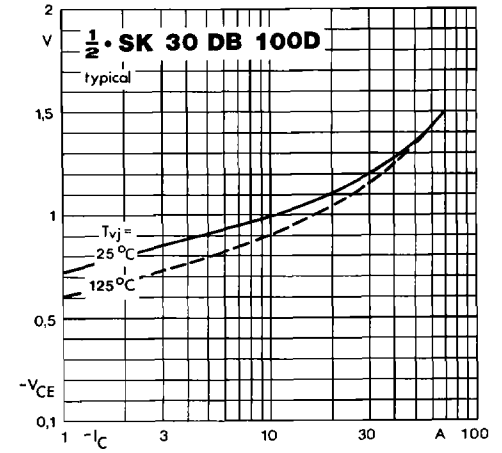


Fig. 11 Inverse diode forward characteristics

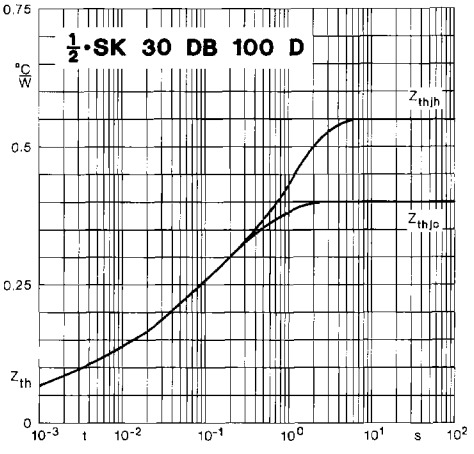


Fig. 12 Transient thermal impedance vs. time

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Case D 11

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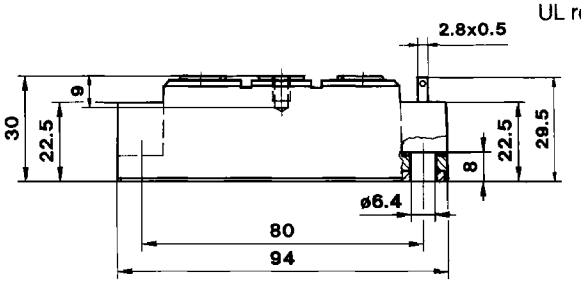

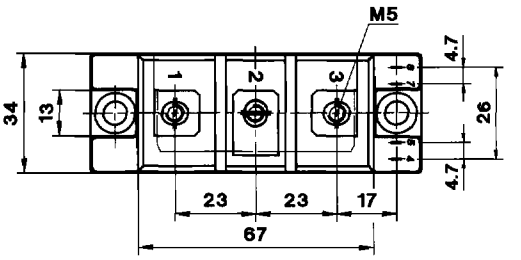

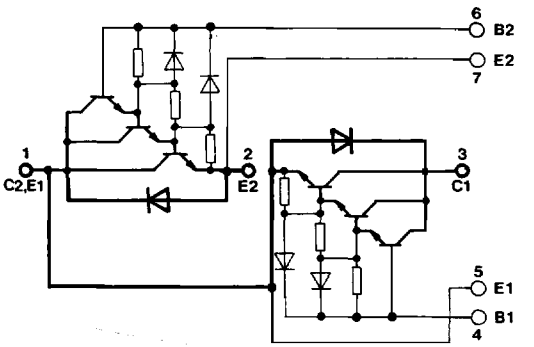

Dimensions in mm

SK 30 DAL 100 D

Case D 21

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